July 2008



FGH60N60SF 600V, 60A Field Stop IGBT

Features

- High current capability
- Low saturation voltage: $V_{CE(sat)} = 2.3V @ I_C = 60A$
- High input impedance •
- Fast switching •
- RoHS compliant •

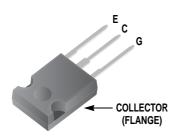
Applications

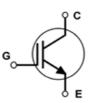
• Induction Heating, UPS, SMPS, PFC



General Description

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Induction Heating, UPS, SMPS and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

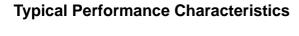
Symbol	Description		Ratings	Units
V _{CES}	Collector to Emitter Voltage		600	V
V _{GES}	Gate to Emitter Voltage		± 20	V
I _C	Collector Current	@ T _C = 25 ^o C	120	A
	Collector Current	@ T _C = 100°C	60	A
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25 ^o C	180	A
P _D	Maximum Power Dissipation	@ T _C = 25°C	378	W
	Maximum Power Dissipation	@ T _C = 100°C	151	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes: 1: Repetitive test, Pulse width limited by max. juntion temperature

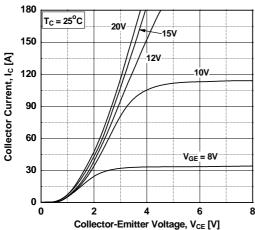
Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.33	°C/W
R _{0JA} Thermal Resistance, Junction to Ambient		-	40	°C/W

	lorking	Device	Dookogo	Packaging	Otype			x Qty
Device Marking Device FGH60N60SF FGH60N60SF			Package Type		Qty per Tube		per Box	
FGH60h	NOUSF	FGH60N60SFTU	TO-247	Tube	30)ea		-
Electric	al Chai	racteristics of the		5°C unless otherwise noted				
Symbol		Parameter	Test	Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics							
BV _{CES}	Collector	to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C}$; = 250μΑ	600	-	-	V
ΔΒV _{CES} ΔΤ _J	Temperat Voltage	ure Coefficient of Breakdown	V _{GE} = 0V, I _C	$V_{GE} = 0V, I_{C} = 250 \mu A$		0.4	-	V/ºC
I _{CES}	Collector	Cut-Off Current	$V_{CE} = V_{CES}$, V _{GE} = 0V	-	-	250	μΑ
I _{GES}	G-E Leak	age Current	$V_{GE} = V_{GES}$, V _{CE} = 0V	-	-	±400	nA
On Charac	teristics		- I					
V _{GE(th)}		shold Voltage	I _C = 250μA,	$V_{CE} = V_{GE}$	4.0	5.0	6.5	V
			$I_{\rm C} = 60$ A, $V_{\rm G}$		-	2.3	2.9	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage			$I_{C} = 60A, V_{GE} = 15V,$ $T_{C} = 125^{\circ}C$		2.5	-	V
Dynamic C	haracteris	tics	1 -		-	1		Į
C _{ies}	Input Cap			$V_{CE} = 30V, V_{GE} = 0V,$		2820	-	pF
C _{oes}	Output Ca	apacitance				350	-	pF
C _{res}	Reverse ⁻	Transfer Capacitance	f = 1MHz		-	140	-	pF
			ł		-1	l		
Switching	-		1		-			
t _{d(on)}		Delay Time	_			22 42	-	ns
t _r	Rise Time	Delay Time			-	134	-	ns
t _{d(off)} t _f	Fall Time			$\label{eq:V_CC} \begin{array}{l} V_{CC} = 400 V, \ I_C = 60 A, \\ R_G = 5 \Omega, \ V_{GE} = 15 V, \\ \mbox{Inductive Load, } T_C = 25^o C \end{array}$		31	62	ns ns
ч E _{on}		Switching Loss				1.79	-	mJ
E _{off}		Switching Loss	_		-	0.67	-	mJ
E _{ts}		ching Loss			-	2.46	-	mJ
t _{d(on)}		Delay Time			-	22	-	ns
t _r	Rise Time	; ;	1		-	44	-	ns
t _{d(off)}	Turn-Off	Delay Time	V _{CC} = 400V, I _C = 60A,		-	144	-	ns
t _f	Fall Time		$R_G = 5\Omega, V_G$	R _G = 5Ω, V _{GE} = 15V,	-	43	-	ns
E _{on}	Turn-On S	Switching Loss	Inductive Lo	ad, T _C = 125 ^o C	-	1.88	-	mJ
E _{off}	Turn-Off S	Switching Loss			-	1.0	-	mJ
E _{ts}	Total Swit	ching Loss			-	2.88	-	mJ
Qg	Total Gate	e Charge			-	198	-	nC
Q _{ge}	Gate to E	mitter Charge	$V_{CE} = 400V,$	I _C = 60A,	-	22	-	nC
Q _{gc}	Cata ta C	ollector Charge	V _{GE} = 15V		-	106		nC









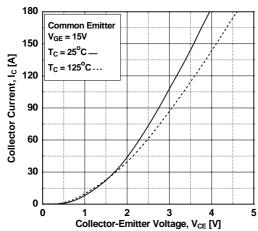


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

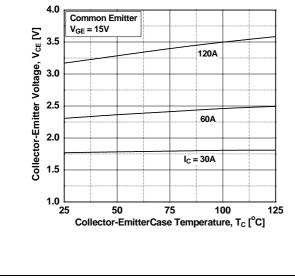


Figure 2. Typical Output Characteristics

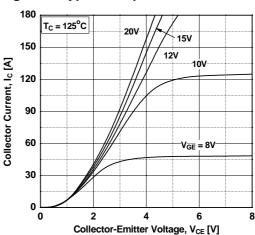


Figure 4. Transfer Characteristics

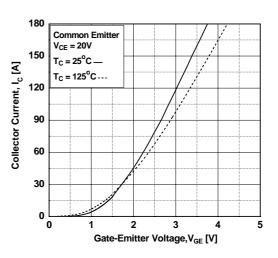
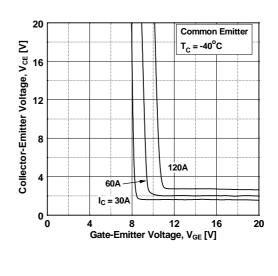
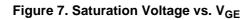
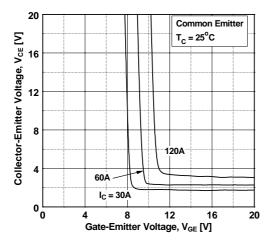


Figure 6. Saturation Voltage vs. V_{GE}

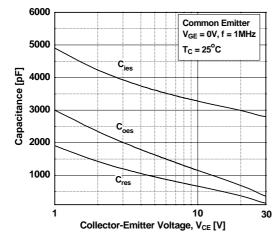


Typical Performance Characteristics











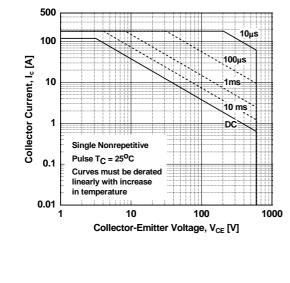


Figure 8. Saturation Voltage vs. V_{GE}

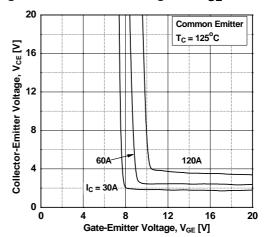


Figure 10. Gate charge Characteristics

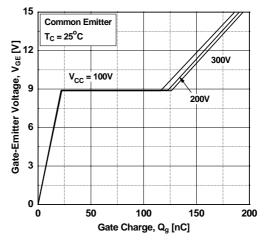
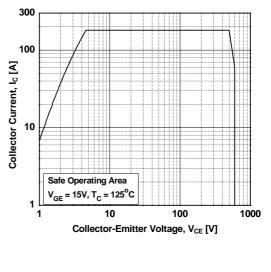
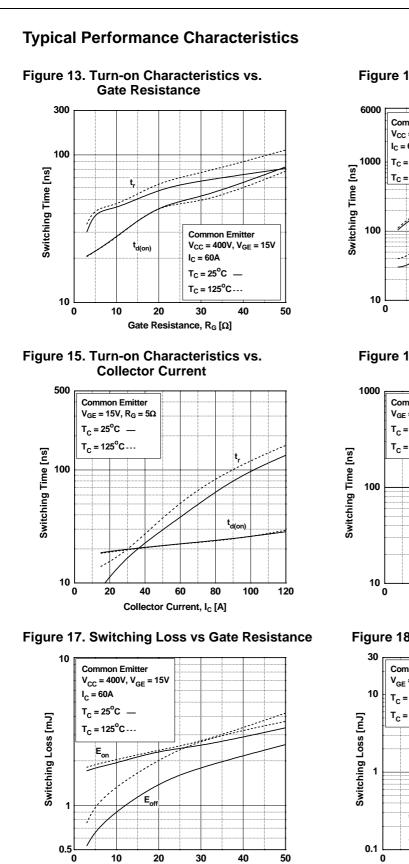
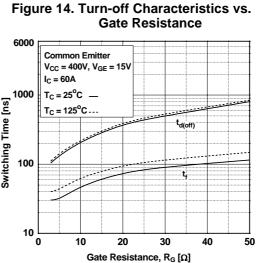


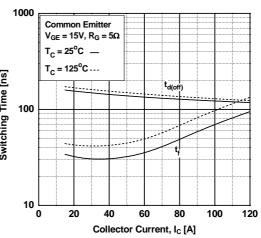
Figure 12. Turn off Switching SOA Characteristics



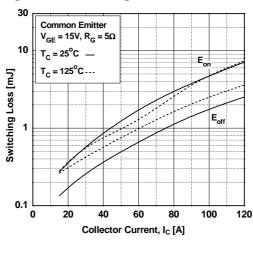












10

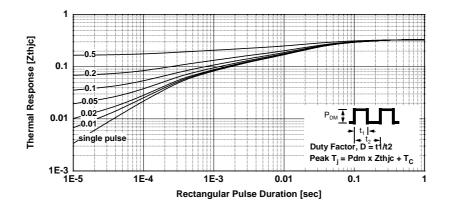
Gate Resistance, R_G [Ω]

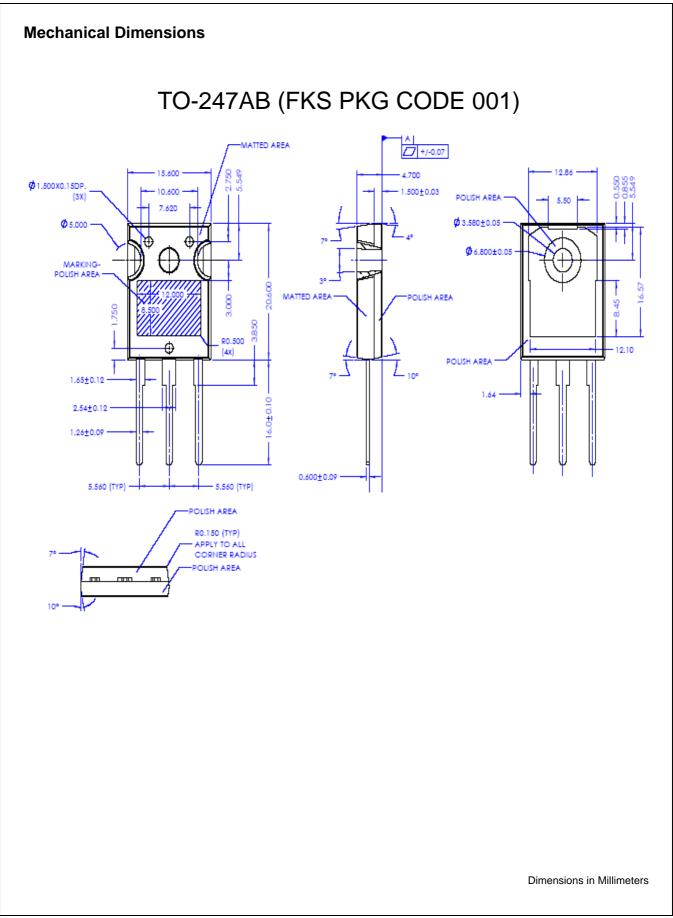
40

FGH60N60SF 600V, 60A Field Stop IGBT

Typical Performance Characteristics

Figure 19. Transient Thermal Impedance of IGBT







SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidianries, and is not intended to be an exhaustive list of all such trademarks.

Build it Now™	FPS™	PDP SPM™	The Power Franchise [®]
CorePLUS™	F-PFS™	Power-SPM [™]	the
CorePOWER™	FRFET [®]	PowerTrench [®]	puwer
CROSSVOLT™	Global Power Resource SM	Programmable Active Droop™	I franchise TinyBoost™
CTL™	Green FPS™	QFET®	
Current Transfer Logic™	Green FPS™ e-Series™	QS™	TinyBuck™ TinyLogio®
EcoSPARK [®]	GTO™	Quiet Series [™]	TinyLogic [®] TINYOPTO™
EfficentMax™	IntelliMAX™	RapidConfigure™	TinyPower™
EZSWITCH™ *	ISOPLANAR™	Saving our world, 1mW at a time™	TinyPWM™
	MegaBuck™	SmartMax™	TinyWire™
	MICROCOUPLER™	SMART START™	
R	MicroFET™	SPM®	\mathcal{N}
	MicroPak™	STEALTH™	/ SerDes
Fairchild®	MillerDrive™	SuperFET™	UHC [®]
Fairchild Semiconductor®	MotionMax™	SuperSOT™-3	Ultra FRFET™
FACT Quiet Series™	Motion-SPM™	SuperSOT™-6	UniFET™
FACT®	OPTOLOGIC®	SuperSOT™-8	VCX™
FAST®	OPTOPLANAR®	SupreMOS™	VisualMax™
FastvCore™	®	SyncFET™	
FlashWriter [®] *	U		

* EZSWITCH™ and FlashWriter[®] are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Farichild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Farichild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.